



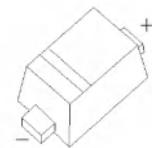
迈拓电子
MAITUO ELECTRONIC

BAT54X Schottky Barrier Diode



FEATURES

- Extremely Fast Switching Speed
- Low Forward Voltage



MARKING: JV

SOD-523

Maximum Ratings @Ta=25°C

Parameter	Symbol	Limit	Unit
Non-repetitive peak reverse voltage	V _{RM}	30	V
DC blocking voltage	V _R	21	V
Average rectified output current	I _O	100	mA
Forward continuous current	I _F	200	mA
Repetitive peak forward current	I _{FRM}	300	mA
Bcb!fYdYHj YDYU Forward surge current 4 mA, "a g	I _{FSM}	600	mA
Power dissipation	P _d	150	mW
Thermal resistance junction to ambient	R _{θJA}	667	°C/W
Junction temperature	T _J	125	°C
Storage temperature range	T _{STG}	-55~+150	°C

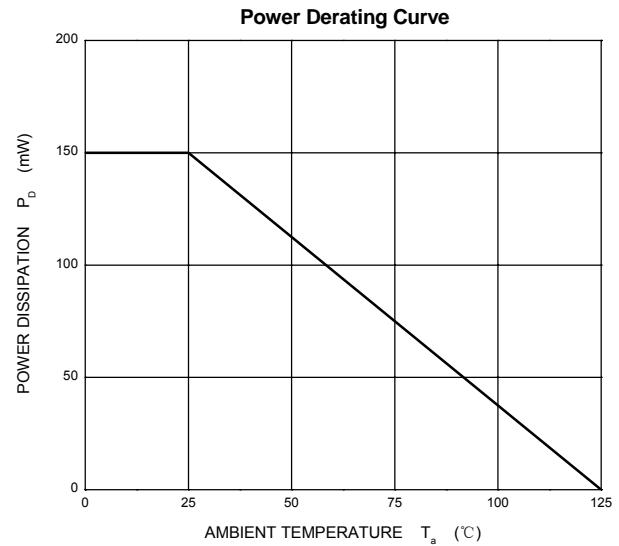
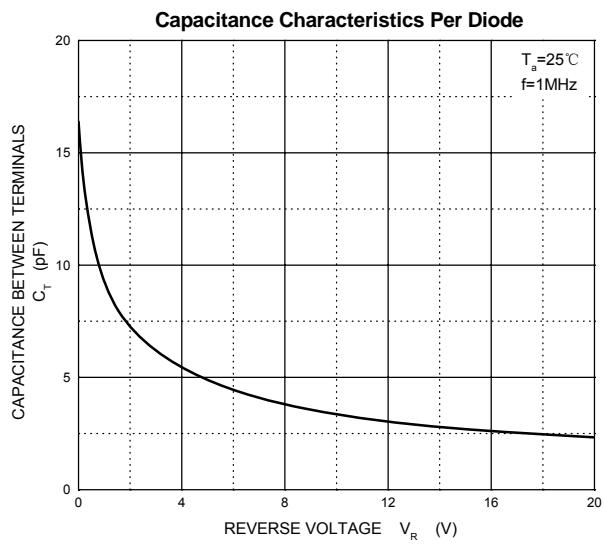
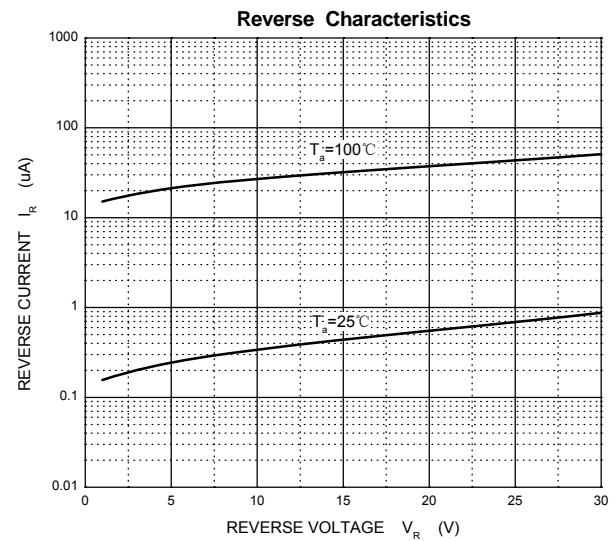
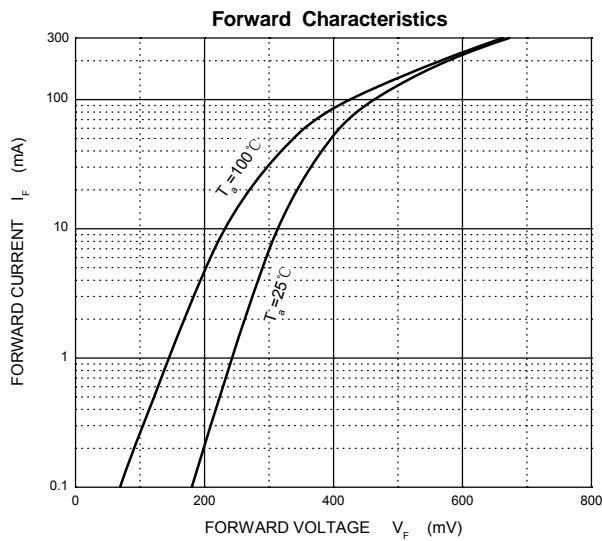
Electrical Characteristics @Ta=25°C

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	V _(BR)	I _R =100μA	30			V
Forward voltage	V _{F1}	I _F =0.1mA			240	mV
	V _{F2}	I _F =1.0mA			320	mV
	V _{F3}	I _F =10mA			400	mV
	V _{F4}	I _F =30mA			500	mV
	V _{F5}	I _F =100mA			1000	mV
Reverse current	I _R	V _R =25V			2.0	uA
Reverse recovery time	t _{rr}	I _F =10mA, I _R =10mA to 1mA , R _L =100 Ω			5.0	ns
Capacitance between terminals	C _T	V _R =1V,f=1MHz			10	pF



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Typical Characteristics



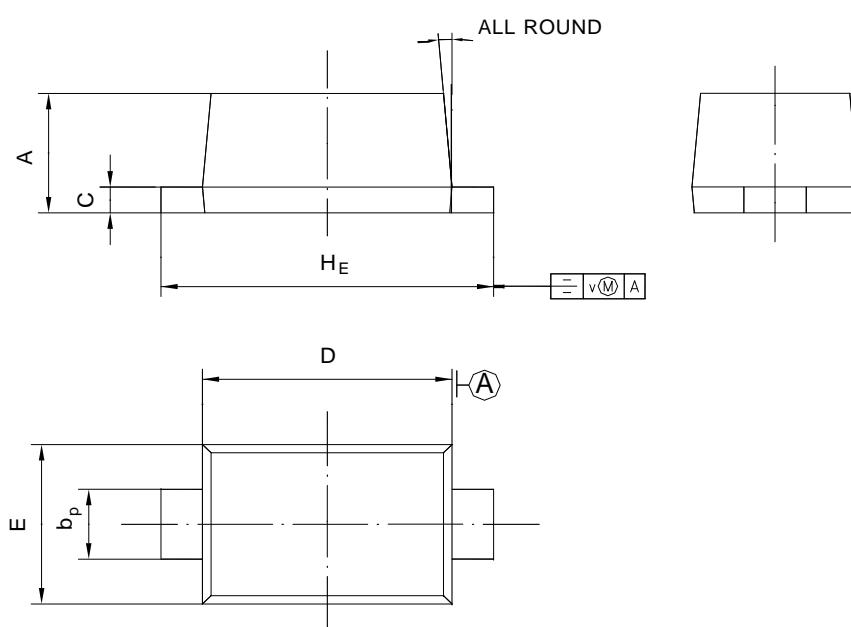


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PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-523



UNIT	A	b _p	C	D	E	H _E	V	∠
mm	0.68 0.58	0.4 0.3	0.135 0.100	1.25 1.15	0.85 0.75	1.7 1.5	0.1	5°